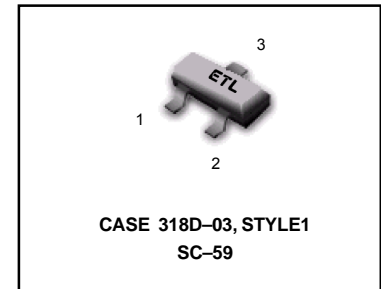
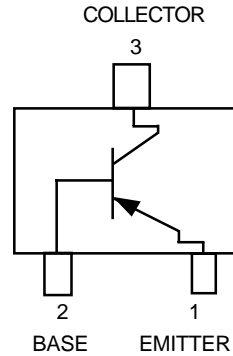


PNP General Purpose Amplifier Transistor Surface Mount

MSB709-RT1



MAXIMUM RATINGS (T_A = 25 °C)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{(BR)CBO}	-60	Vdc
Collector-Emitter Voltage	V _{(BR)CEO}	-45	Vdc
Emitter-Base Voltage	V _{(BR)EBO}	-7.0	Vdc
Collector Current - Continuous	I _C	-100	mAdc
Collector Current - Peak	I _{C(P)}	-200	mAdc

THERMAL CHARACTERISTICS

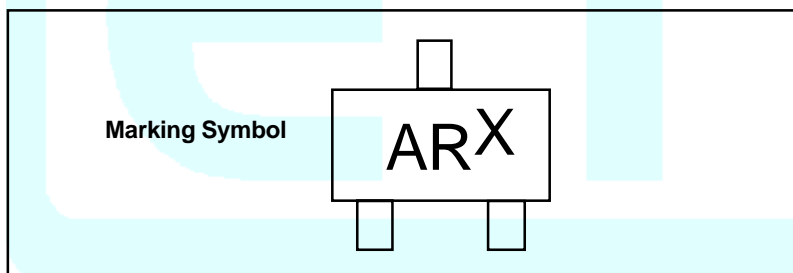
Characteristic	Symbol	Max	Unit
Power Dissipation	P _D	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

Characteristic	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage (I _C = -2.0mAdc, I _B = 0)	V _{(BR)CEO}	-45	—	Vdc
Collector-Base Breakdown Voltage (I _C = -10μAdc, I _E = 0)	V _{(BR)CBO}	-60	—	Vdc
Emitter-Base Breakdown Voltage (I _E = -10μAdc, I _C = 0)	V _{(BR)EBO}	-7.0	—	Vdc
Collector-Base Cutoff Current (V _{CB} = -45Vdc, I _E = 0)	I _{CBO}	—	-0.1	μAdc
Collector-Emitter Cutoff Current (V _{CE} = -10Vdc, I _B = 0)	I _{CEO}	—	-100	nAdc
DC Current Gain ⁽¹⁾ (V _{CE} = -10Vdc, I _C = -2.0mAdc)	h _{FE1}	210	340	—
Collector-Emitter Saturation Voltage (I _C = -100mAdc, I _B = -10mAdc)	V _{CE(sat)}	—	-0.5	Vdc

1. Pulse Test: Pulse Width ≤ 300 μs, D.C. ≤ 2%.

DEVICE MARKING



The "X" represents a smaller alpha digit Date Code. The Date Code indicates the actual month in which the part was manufactured.